

↙
The object and subject of the invention are achieved by a process for the metallization of at least one insulating layer of an electronic or microelectronic component, whose layer thickness is at most 50 μm , wherein firstly

- at least one insulating layer is applied to the substrate and is activated by treatment with an activator,
- then another insulating layer is applied and patterned, and lastly
- the first insulation layer is seeded and metallized. --

On page 5, lines 13-14, replace the paragraph with:

↘
-- The thickness of the insulating layer is preferably between 0.05 and 50 μm , particularly preferably between 0.1 and 20 μm .
--

Remarks:

Reconsideration of the application is requested.

Claims 4-7 remain in the application.

In item 2 on page 2 of the Office action dated March 8, 2002, the disclosure has been objected to because of the following